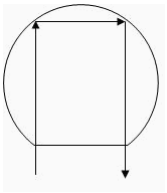
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	406.50 +/- 11.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00um	ADE 100%, SEMI MF1530.
	7.0	Bow	<60.00µm	ADE 100%, SEMI MF1390
	8.0	Warp	<60.00µm	ADE 100%, SEMI MF1390
	9.0	Edge Chips	0	Bright Light, 100%
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	13.0	Handle Thickness	400.00 +/- 10.00 µm	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	1~5 Ohm-cm	Wafer Vendor
	17.0	Backside Finish	Polished with oxide, lasermark and light handling marks	Wafer Vendor
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	5,000.00 +/- 500.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle and / or device Wafer	
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor
	22.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	23.0	Nominal Thickness	6.00 +/- 0.50 µm	FTIR, 100% 9-Pt (note3)
	24.0	Distance to device silicon edge from wafer edge	<= 2mm	Typical by Process
	25.0	Edge Removal Depth in Handle	<100 um	Graranteed by process
	26.0	Device Doping Type	N	Wafer Vendor
	27.0	Device Dopant	Phosphorous	Wafer Vendor
	28.0	Device Resistivity	1~10 Ohm-cm	Wafer Vendor
	29.0	Oxygen Concentration	<=14 ppma	Wafer Vendor, New ASTM
	30.0	Dislocation Etch Pit Density	<=100 /cm2	Wafer Vendor
	31.0	Voids	none	Bright Light, 100% (note 2)
	32.0	Scratches	0	Bright Light, 100% (note 2)
	33.0	Haze	none	Bright Light, 100% (note 2)

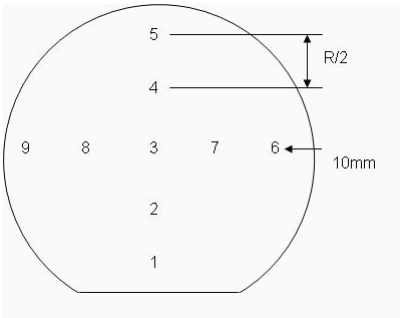
Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information